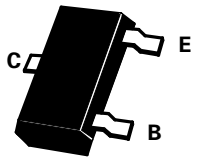
SOT23 NPN SILICON PLANAR SWITCHING TRANSISTOR

ISSUE 2 – SEPTEMBER 95 ✪

BSS79B BSS79C

PARTMARKING DETAILS - BSS79B - CE
BSS79C - CF



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Peak Pulse Current	I_{CM}	800	mA
Power Dissipation at T_{amb}=25°C	P_{TOT}	330	mW
Operating and Storage Temperature Range	t_j:t_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER		SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	75		V	I_C=10μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	40		V	I_C=10mA
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	6		V	IE=10μA
Collector Base Cut-Off Current		I_{CBO}		10 10	nA μA	V_{CB}=60V V_{CB}=60V, T_{amb}=150°C
Emitter Base Cut-Off Current		I_{EBO}		10	nA	V_{BE}=3.0V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$		0.3 1.0	V V	I_C=150mA, I_B=15mA I_C=500mA, I_B=50mA
Static Forward Current Transfer Ratio	BSS79B BSS79C	h_{FE}	40 100	120 300		I_C=150mA, V_{CE}=10V I_C= 150mA, V_{CE}=10V
Transition Frequency		f_T	250		MHz	V_{CE}=20V, I_C=20mA f=100MHz
Collector-Base Capacitance		C_{obo}		8	pF	V_{CB}=10V, f=1MHz
Delay Time		t_d		10	ns	V_{CC}=30V, I_C=150mA I_{B1}=I_{B2}=15mA
Rise Time		t_r		10	ns	
Storage Time		t_s		225	ns	V_{CC}=30V, I_C=150mA I_{B1}=I_{B2}=15mA
Fall Time		t_f		60	ns	

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